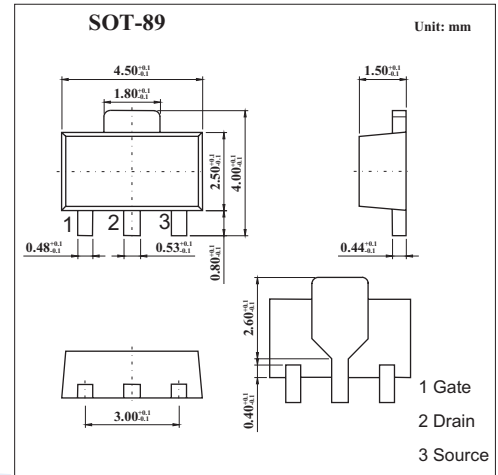


P-Channel MOS Silicon FET

2SJ287

■ Features

- Low on resistance
- Very high-speed switching
- Low-voltage drive



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain to source voltage $V_{GS}=0$	V_{DSS}	-30	V
Gate to source voltage $V_{DS}=0$	V_{GSS}	± 15	V
Drain current (DC)	I_D	-500	m A
Drain current(pulse) *	I_D	-2	A
Power dissipation	P_D	3.5	W
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

* $PW \leq 10 \mu\text{s}$; $d \leq 1\%$.

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Drain cut-off current	I_{DSS}	$V_{DS}=-30V, V_{GS}=0$			-100	μA
Gate leakage current	I_{GSS}	$V_{GS}=\pm 12V, V_{DS}=0$			± 10	μA
Gate cut-off voltage	$V_{GS(off)}$	$V_{DS}=-10V, I_D=-1\text{mA}$	-1.0		-2.0	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS}=-10V, I_D=-250\text{mA}$	240	400		ms
Drain to source on-state resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-250\text{mA}$		1.5	2.2	Ω
		$V_{GS}=-4V, I_D=-250\text{mA}$		2.2	3.3	Ω
Input capacitance	C_{iss}	$V_{DS}=-10V, V_{GS}=0, f=1\text{MHz}$		50		pF
Output capacitance	C_{oss}			35		pF
Reverse transfer capacitance	C_{rss}			10		pF
Turn-on delay time	$t_{d(on)}$				7	ns
Rise time	t_r	$V_{DD}=-15V, I_D=-250\text{mA}, R_L=60\Omega$		10		ns
Turn-off delay time	$t_{d(off)}$			35		ns
Fall time	t_f				20	ns

■ Marking

Marking	JD
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